

(19) United States

(12) Patent Application Publication (10) Pub. No.: US 2024/0215243 A1 TSUTSUMI et al.

Jun. 27, 2024 (43) **Pub. Date:**

(54) THREE-DIMENSIONAL MEMORY DEVICE WITH THROUGH-STACK CONTACT VIA STRUCTURES AND METHOD OF MAKING THE SAME

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(21) Appl. No.: 18/532,221

Filed: Dec. 7, 2023 (22)

Related U.S. Application Data

(63) Continuation-in-part of application No. 18/351,828, filed on Jul. 13, 2023, Continuation-in-part of application No. 18/455,988, filed on Aug. 25, 2023, which is a continuation-in-part of application No. 18/361, 629, filed on Jul. 28, 2023.

Provisional application No. 63/476,488, filed on Dec. 21, 2022, provisional application No. 63/499,819, filed on May 3, 2023.

Publication Classification

(51) Int. Cl. H10B 43/27 (2006.01)

U.S. Cl. (52)

CPC *H10B 43/27* (2023.02)

(57)ABSTRACT

A memory device includes an alternating stack of insulating layers and electrically conductive layers, and comprising stepped surfaces, a memory opening vertically extending through each layer within the alternating stack, a memory opening fill structure located in the memory opening and including a vertical stack of memory elements and a vertical semiconductor channel, a dielectric material layer that extends from a bottommost vertical step of the stepped surfaces to a topmost vertical step of the stepped surfaces, and a contact via structure including an upper contact via portion having an annular bottom surface that contacts an annular top surface of a first electrically conductive layer of the electrically conductive layers, and a lower contact via portion that vertically extends through a first subset of the electrically conductive layers that underlie the first electrically conductive layer, and the lower contact via portion is narrower than the upper contact via portion.

